

### DESCRIPTION:

The JOC215 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic SSOP4 package. With the robust coplanar double mold structure, JOC215 series provide the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

### MAIN FEATURES

Current transfer ratio (CTR: 600%-7500% @ $I_F=1\text{mA}$ ,  $V_{CE}=2\text{V}$ )

High isolation voltage between input and output

( $V_{iso}=3750\text{Vrms}$ )

Operating temperature up to +110°C

Collector-Emitter voltage  $BV_{CEO} \geq 40\text{V}$

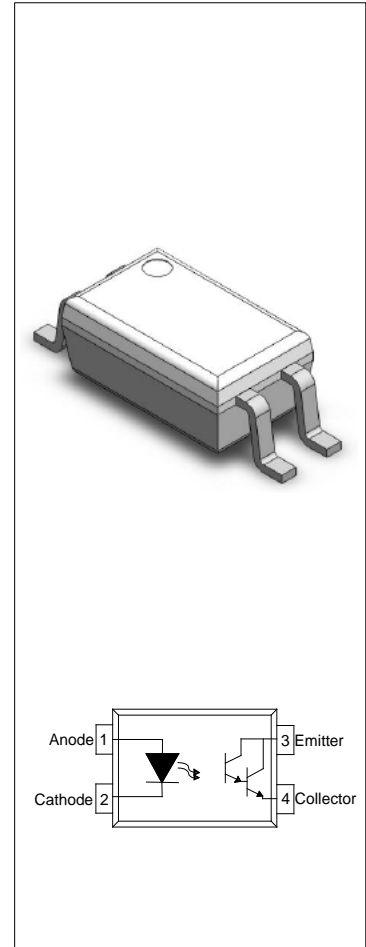
MSL class 1

CQC approved

VDE approved

UL approved

The products comply with RoHS, REACH and HF



### ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	$I_F$	60	mA
	Peak Forward Current	$I_{FP}$	1 <sup>①</sup>	A
	Reverse Voltage	$V_R$	6	V
	Power Dissipation	$P_D$	100	mW
Output	Collector-emitter Voltage	$V_{CEO}$	40	V
	Emitter-collector Voltage	$V_{ECO}$	6	V
	Collector Current	$I_C$	80	mA
	Power Dissipation	$P_C$	150	mW
Total Power Dissipation		$P_{tot}$	250	mW

Isolation Voltage	$V_{iso}$	3750 <sup>②</sup>	Vrms
Operating Temperature	$T_{opr}$	-55~+110	°C
Storage Temperature	$T_{stg}$	-55~+125	°C
Soldering Temperature	$T_{sol}$	260	°C


**NOTE1**: 100μs pulse, 100Hz frequency

**NOTE2**: AC for 1minute, R.H.=40~60%

### ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	$V_F$	$I_F=10mA$	-	-	1.4	V
	Reverse Current	$I_R$	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	$C_t$	$V=0, f=1kHz$	-	10	-	pF
Output	Collector-Emitter dark current	$I_{CEO}$	$V_{CE}=10V, I_F=0$	-	-	100	nA
	Collector-Emitter breakdown voltage	$BV_{CEO}$	$I_C=0.1mA, I_F=0$	40	-	-	V
	Emitter-Collector breakdown voltage	$BV_{ECO}$	$I_E=0.1mA, I_F=0$	6	-	-	V
Transfer Characteristics	Current transfer ratio	$CTR^{①}$	$I_F=1mA, V_{CE}=2V$	600	-	7500	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=20mA, I_C=5mA$	-	0.8	1	V
	Isolation resistance	$R_{IO}$	DC500V 40~60%R.H.	$10^{12}$	$10^{14}$	-	Ω
	Floating Capacitance	$C_{IO}$	$V=0, f=1MHz$	-	0.4	1	pF
	Cut-off Frequency	$f_c$	$V_{CE}=5V, I_C=10mA, R_L=100Ω, -3dB$	-	1	-	kHz
	Rise Time	$t_r$	$V_{CE}=2V, I_C=10mA$	-	95	300	μs
	Fall Time	$t_f$	$R_L=100Ω$	-	84	250	μs

**ORDERING AND MARKING INFORMATION**

<b>MARKING INFORMATION</b>			
		<p>JOC : Company Abbr.                      215 : Part Number                      VYAWW : LOT NO.</p>	
<b>ORDERING INFORMATION</b>			
<b>JOC215(Z)-GV</b>			
<p>JOC – Company Abbr.                      215 – Part Number                      Z – Tape and Reel Option (T1/T2)                      G – Green                      V – VDE Option (V or None)</p>			
<b>Packing Quantity</b>			
<b>Option</b>	<b>Quantity</b>	<b>Quantity – Inner box</b>	<b>Quantity –Outer box</b>
T1	3000 Units/ Reel	3 Reels/Inner box	5 Inner box/Outer box =45k Units
T2	3000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box =45k Units

Characteristics Curves

FIG.1: Forward Current vs. Ambient Temperature

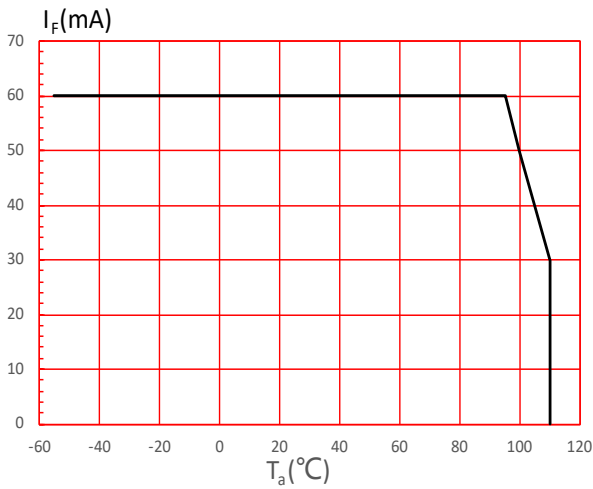


FIG.2: Collector Power Dissipation vs. Ambient Temperature

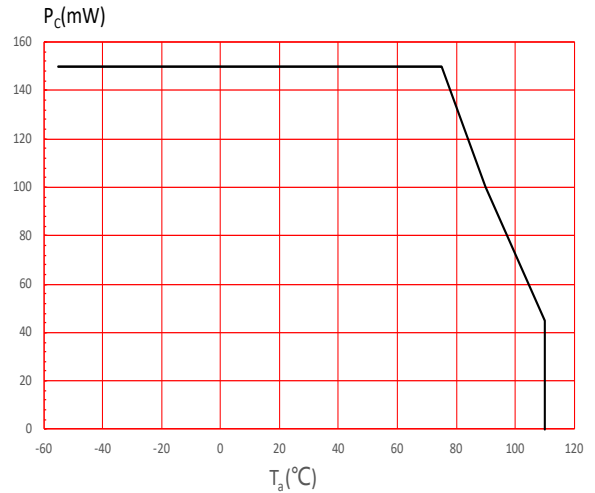


FIG.3: Forward Current vs. Forward Voltage

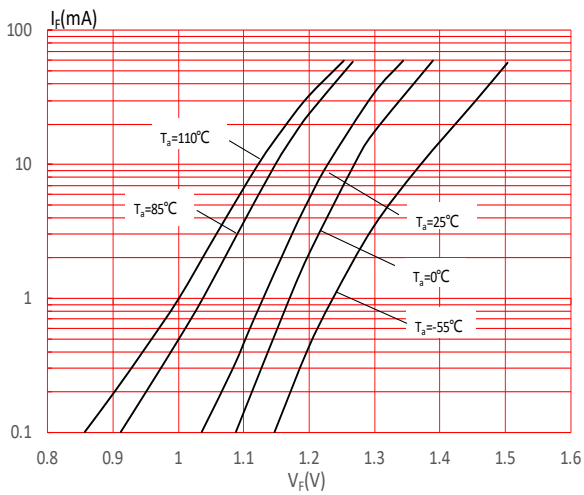


FIG.4: Collector Dark Current vs. Ambient Temperature

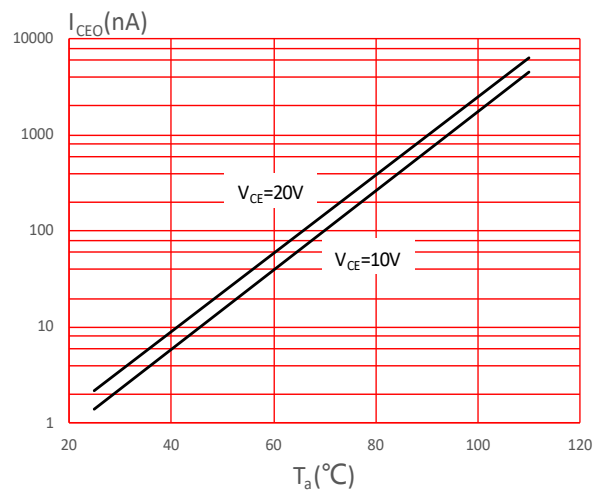


FIG.5: Collector Current vs. Collector-emitter Voltage

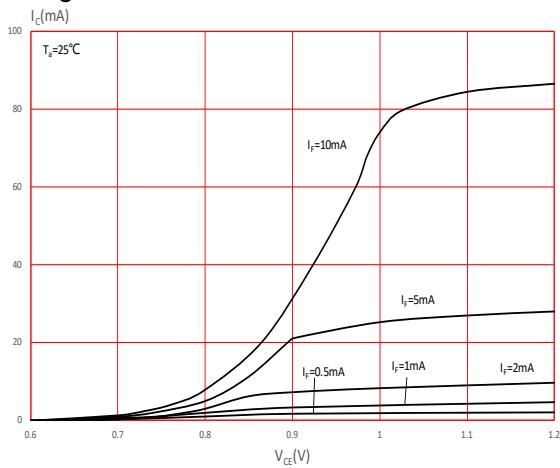
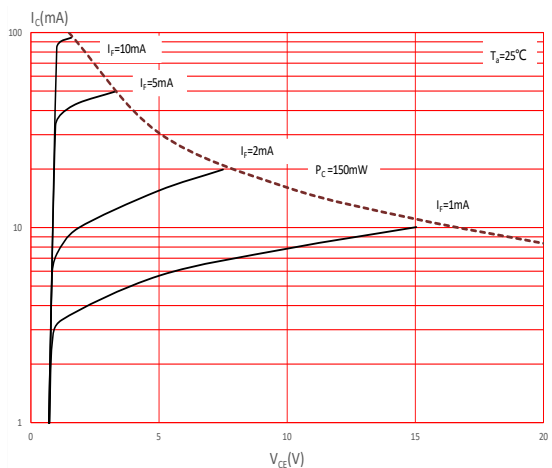
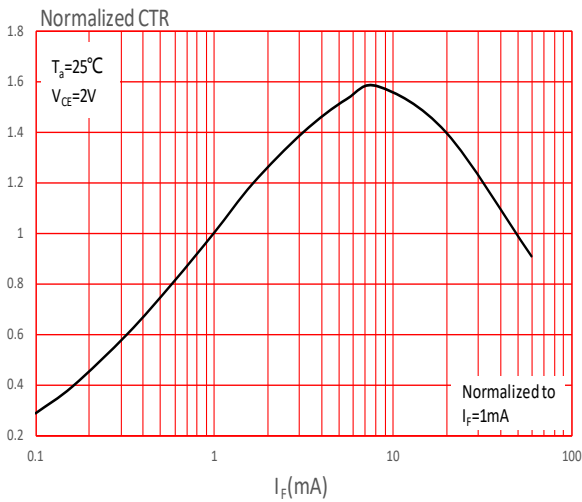


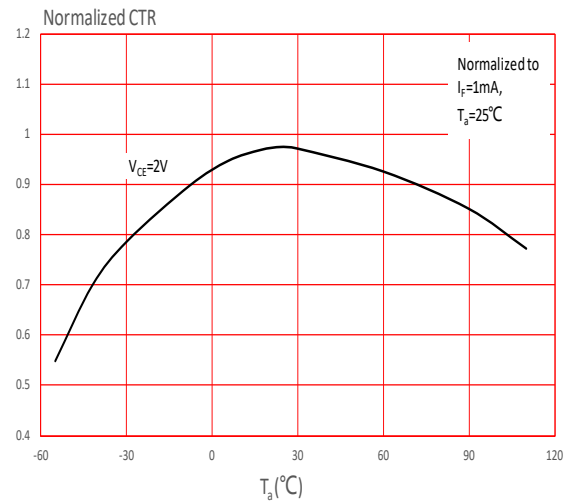
FIG.6: Collector Current vs. Collector-emitter Voltage



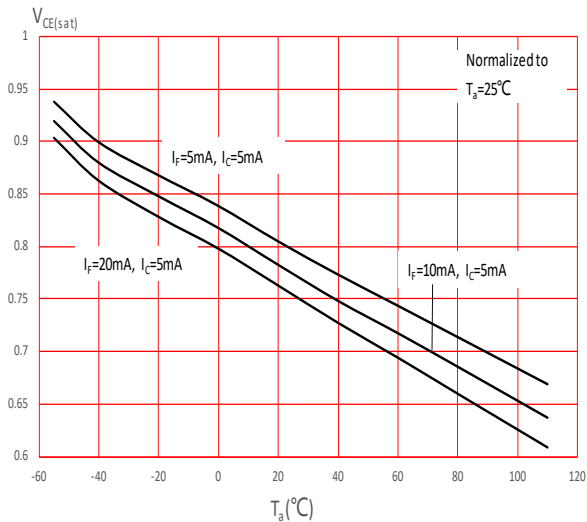
**FIG.7:** Normalized Current Transfer Ratio vs. Forward Current



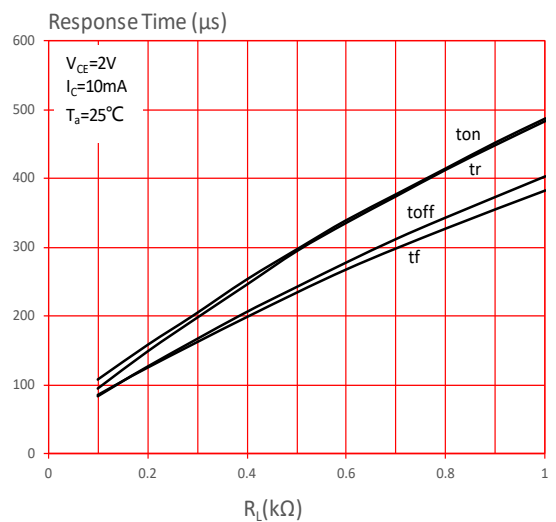
**FIG.8:** Normalized Current Transfer Ratio vs. Ambient Temperature



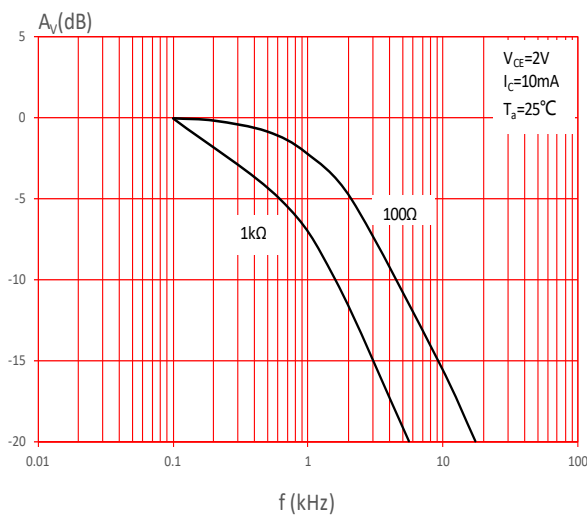
**FIG.9:** Collector-emitter Saturation Voltage vs. Ambient Temperature



**FIG.10:** Response Time vs. Load Resistance



**FIG.11:** Frequency Response



Test Circuits

FIG.12: Test Circuits of Response Time

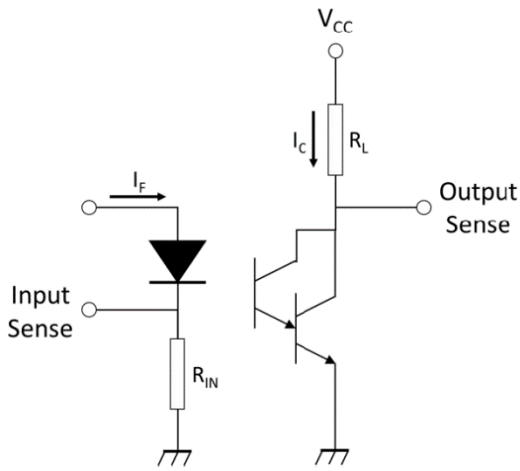


FIG.13: Curves of Response Time

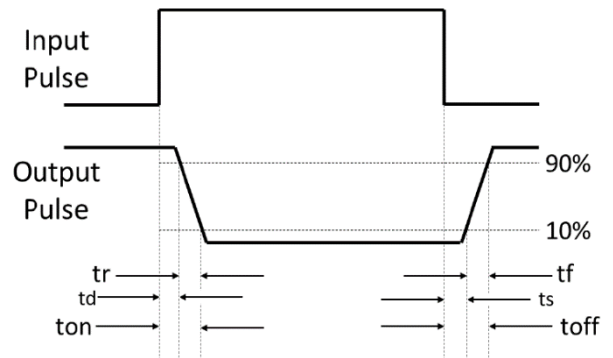
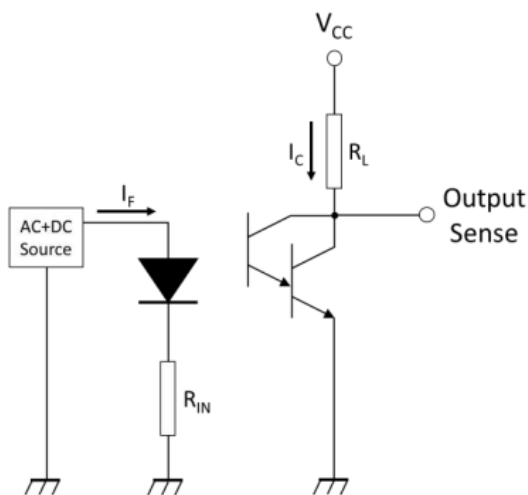
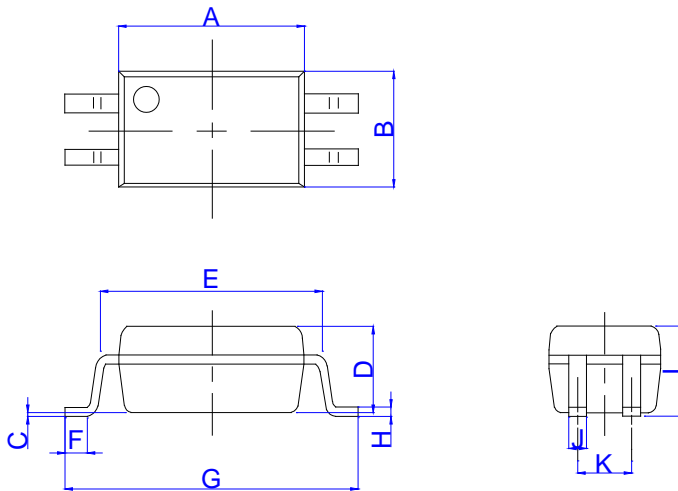


FIG.14: Test Circuits of Frequency Response



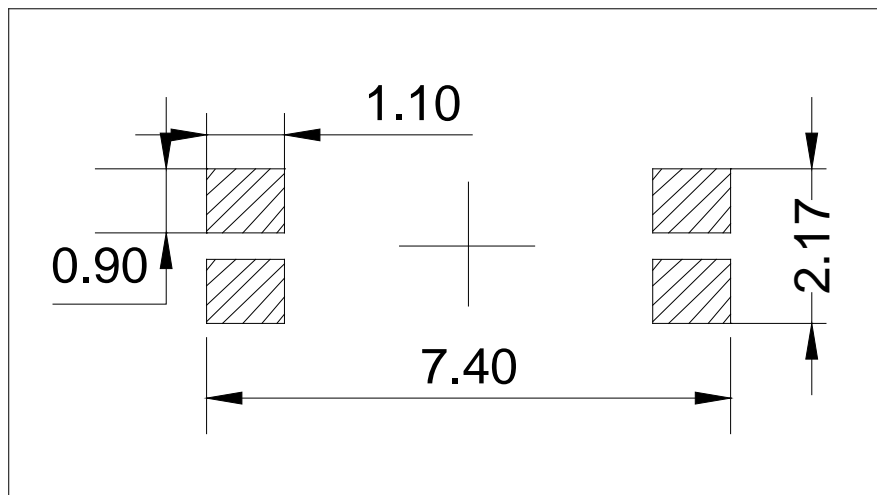
Package Dimension (Unit: mm)

Standard SSOP4 Type:



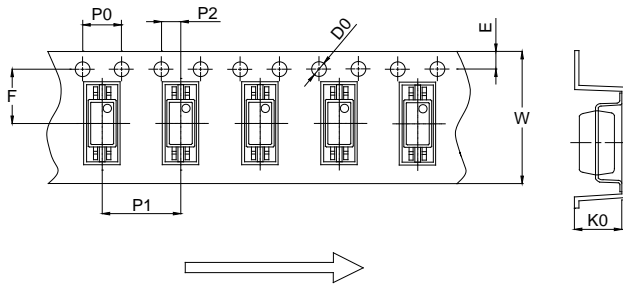
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.20		4.60	0.166		0.182
B	2.50		2.90	0.099		0.115
C		0.10			0.004	
D	1.90		2.10	0.075		0.083
E	4.90		5.50	0.194		0.217
F		0.50			0.020	
G	6.70		7.30	0.265		0.289
H		0.20			0.008	
I		2.10			0.083	
J		0.40			0.016	
K		1.27			0.050	

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)



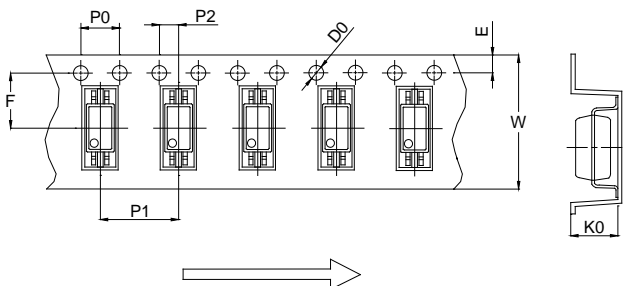
**CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)**

**Option SSOP4(T1)**



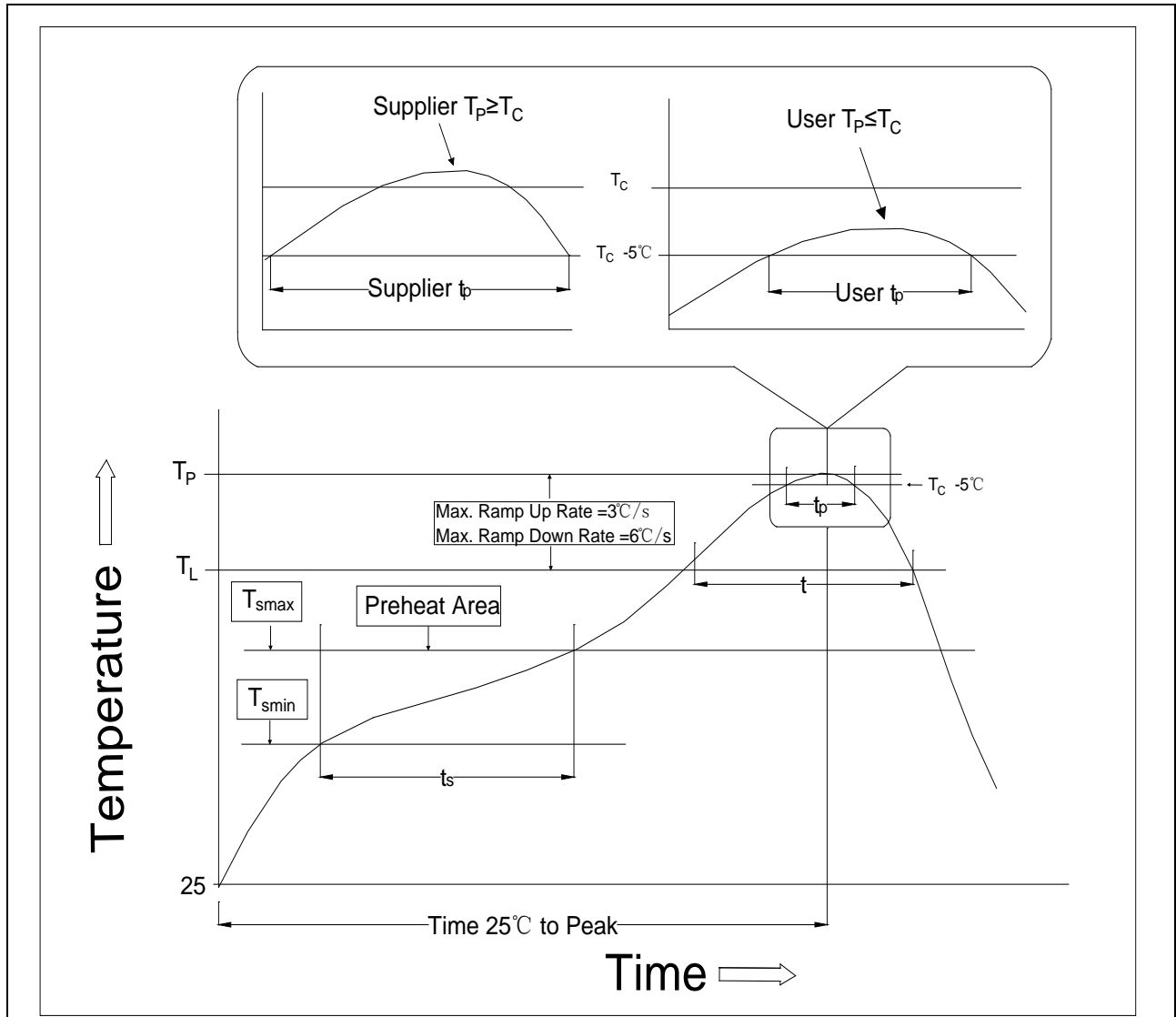
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50			0.059	
K0		2.45			0.096	
P0		4.00			0.157	
P1		8.00			0.315	
P2		2.00			0.079	
E		1.75			0.069	
F		5.50			0.217	
W		12.00			0.472	

**Option SSOP4(T2)**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50			0.059	
K0		2.45			0.096	
P0		4.00			0.157	
P1		8.00			0.315	
P2		2.00			0.079	
E		1.75			0.069	
F		5.50			0.217	
W		12.00			0.472	


REFLOW INFORMATION



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	100	150°C
Temperature Max. (T <sub>smax</sub> )	150	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.	3°C/second max.
Liquidus Temperature (T <sub>L</sub> )	183°C	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235°C+0°C/-5°C	260°C+0°C/-5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.  
Copyright © 2026 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.